

DISCRETE SEMICONDUCTORS

DATA SHEET

BF1101; BF1101R; BF1101WR N-channel dual-gate MOS-FETs

Product specification
Supersedes data of 1999 Feb 01

1999 May 14

N-channel dual-gate MOS-FETs

BF1101; BF1101R; BF1101WR

FEATURES

- Short channel transistor with high forward transfer admittance to input capacitance ratio
- Low noise gain controlled amplifier up to 1 GHz
- Partly internal self-biasing circuit to ensure good cross-modulation performance during AGC and good DC stabilization.

APPLICATIONS

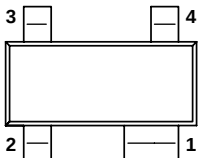
- VHF and UHF applications with 3 to 7 V supply voltage, such as television tuners and professional communications equipment.

DESCRIPTION

Enhancement type N-channel field-effect transistor with source and substrate interconnected. Integrated diodes between gates and source protect against excessive input voltage surges. The BF1101, BF1101R and BF1101WR are encapsulated in the SOT143B, SOT143R and SOT343R plastic packages respectively.

PINNING

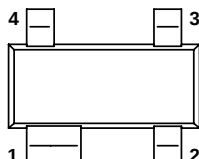
PIN	DESCRIPTION
1	source
2	drain
3	gate 2
4	gate 1



Top view MSB035

BF1101R marking code: NCp.

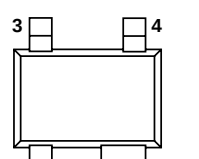
Fig.2 Simplified outline (SOT143R).



Top view MSB014

BF1101 marking code: NDp.

Fig.1 Simplified outline (SOT143B).



Top view MSB842

BF1101WR marking code: NC.

Fig.3 Simplified outline (SOT343R).

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{DS}	drain-source voltage		–	–	7	V
I_D	drain current		–	–	30	mA
P_{tot}	total power dissipation		–	–	200	mW
$ y_{fs} $	forward transfer admittance		25	30	–	mS
C_{ig1-ss}	input capacitance at gate 1		–	2.2	2.7	pF
C_{rss}	reverse transfer capacitance	$f = 1\text{ MHz}$	–	25	35	fF
F	noise figure	$f = 800\text{ MHz}$	–	1.7	2.5	dB
X_{mod}	cross-modulation	input level for $k = 1\%$ at 40 dB AGC	100	–	–	dB μ V
T_j	operating junction temperature		–	–	150	°C

CAUTION

This product is supplied in anti-static packing to prevent damage caused by electrostatic discharge during transport and handling. For further information, refer to Philips specs.: SNW-EQ-608, SNW-FQ-302A and SNW-FQ-302B.

N-channel dual-gate MOS-FETs

BF1101; BF1101R; BF1101WR

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

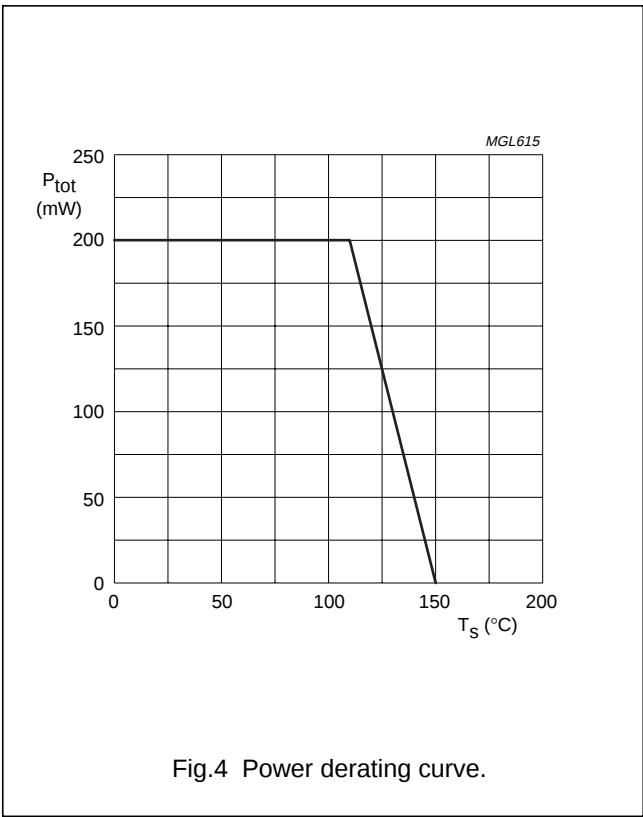
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{DS}	drain-source voltage		–	7	V
I _D	drain current		–	30	mA
I _{G1}	gate 1 current		–	±10	mA
I _{G2}	gate 2 current		–	±10	mA
P _{tot}	total power dissipation	T _s ≤ 110 °C; note 1	–	200	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	operating junction temperature		–	+150	°C

Note

1. T_s is the temperature of the soldering point of the source lead.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-s}	thermal resistance from junction to soldering point	200	K/W



N-channel dual-gate MOS-FETs

BF1101; BF1101R; BF1101WR

STATIC CHARACTERISTICS

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{G1-S} = V_{G2-S} = 0$; $I_D = 10\text{ }\mu\text{A}$	7	–	V
$V_{(BR)G1-SS}$	gate 1-source breakdown voltage	$V_{G2-S} = V_{DS} = 0$; $I_{G1-S} = 10\text{ mA}$	7	16	V
$V_{(BR)G2-SS}$	gate 2-source breakdown voltage	$V_{G1-S} = V_{DS} = 0$; $I_{G2-S} = 10\text{ mA}$	7	16	V
$V_{(F)S-G1}$	forward source-gate 1 voltage	$V_{G2-S} = V_{DS} = 0$; $I_{S-G1} = 10\text{ mA}$	0.5	1.5	V
$V_{(F)S-G2}$	forward source-gate 2 voltage	$V_{G1-S} = V_{DS} = 0$; $I_{S-G2} = 10\text{ mA}$	0.5	1.5	V
$V_{G1-S(th)}$	gate 1-source threshold voltage	$V_{G2-S} = 4\text{ V}$; $V_{DS} = 5\text{ V}$; $I_D = 100\text{ }\mu\text{A}$	0.3	1.0	V
$V_{G2-S(th)}$	gate 2-source threshold voltage	$V_{G1-S} = 5\text{ V}$; $V_{DS} = 5\text{ V}$; $I_D = 100\text{ }\mu\text{A}$	0.3	1.2	V
I_{DSX}	drain-source current	$V_{G2-S} = 4\text{ V}$; $V_{DS} = 5\text{ V}$; $R_{G1} = 120\text{ k}\Omega$; note 1	8	16	mA
I_{G1-SS}	gate 1 cut-off current	$V_{G2-S} = V_{DS} = 0$; $V_{G1-S} = 5\text{ V}$	–	50	nA
I_{G2-SS}	gate 2 cut-off current	$V_{G1-S} = V_{DS} = 0$; $V_{G2-S} = 4\text{ V}$	–	20	nA

Note

1. R_{G1} connects G_1 to $V_{GG} = 5\text{ V}$; see Fig.21.

DYNAMIC CHARACTERISTICS

Common source; $T_{amb} = 25\text{ }^{\circ}\text{C}$; $V_{G2-S} = 4\text{ V}$; $V_{DS} = 5\text{ V}$; $I_D = 12\text{ mA}$; unless otherwise specified.

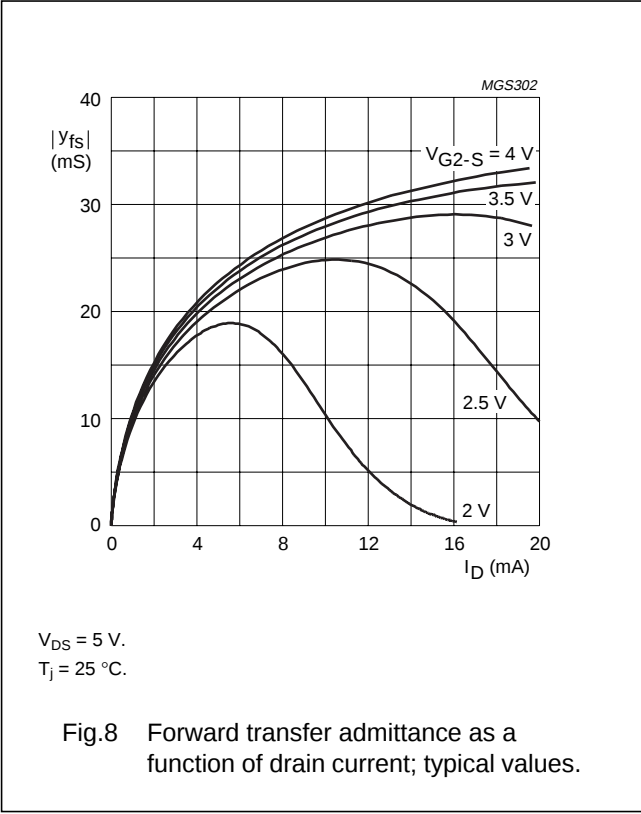
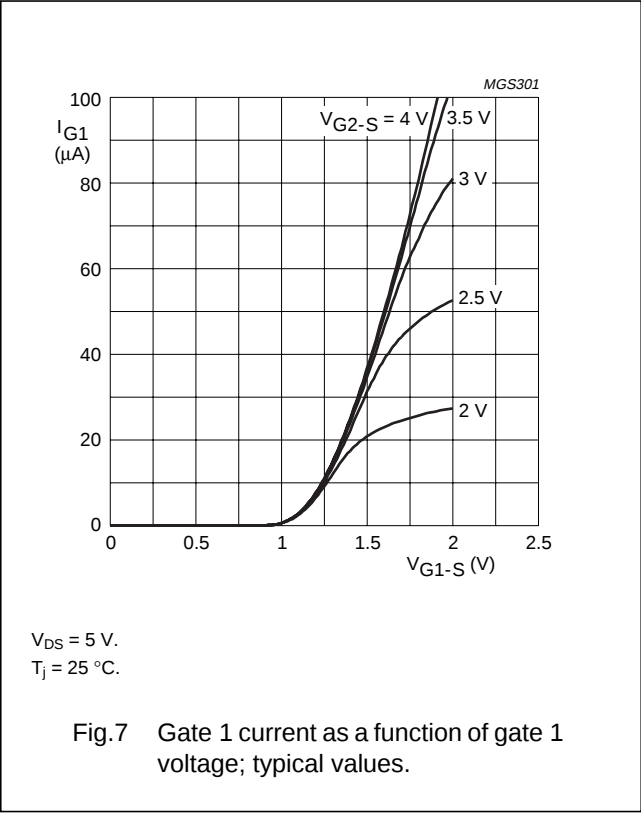
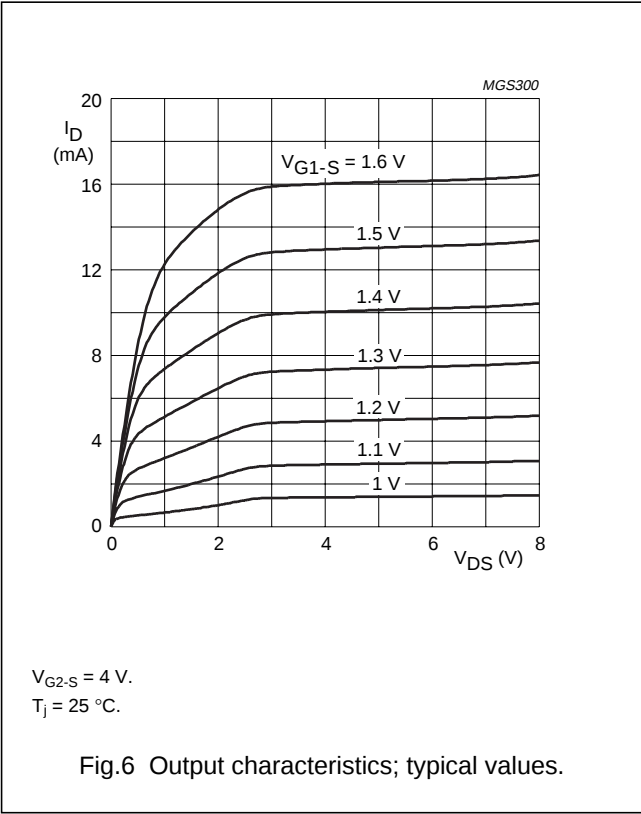
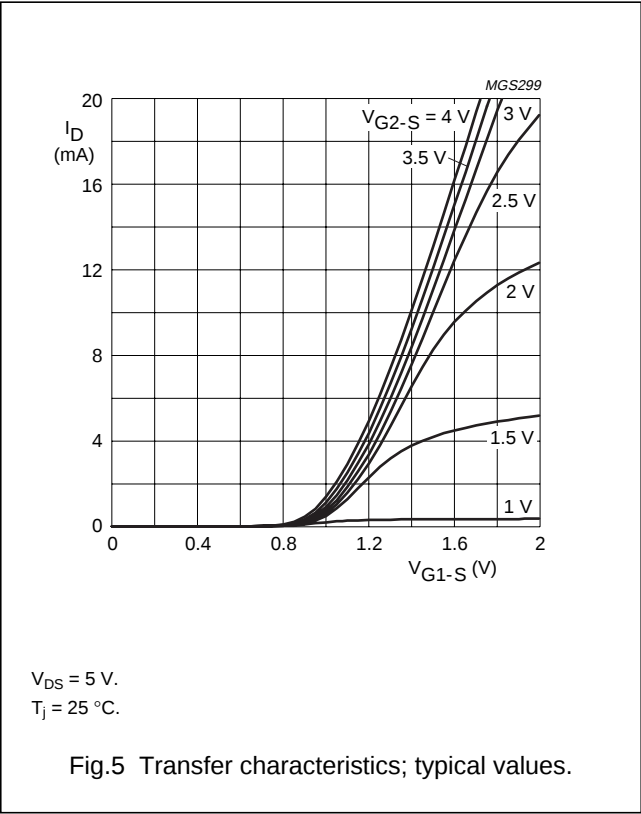
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$ y_{fs} $	forward transfer admittance	pulsed; $T_j = 25\text{ }^{\circ}\text{C}$	25	30	40	mS
C_{ig1-ss}	input capacitance at gate 1	$f = 1\text{ MHz}$	–	2.2	2.7	pF
C_{ig2-ss}	input capacitance at gate 2	$f = 1\text{ MHz}$	–	1.6	–	pF
C_{oss}	output capacitance	$f = 1\text{ MHz}$	–	1.2	–	pF
C_{rss}	reverse transfer capacitance	$f = 1\text{ MHz}$	–	25	35	fF
F	noise figure	$f = 800\text{ MHz}$; $Y_S = Y_{S\text{ opt}}$	–	1.7	2.5	dB
X_{mod}	cross-modulation	input level for $k = 1\%$ at 0 dB AGC; $f_w = 50\text{ MHz}$; $f_{unw} = 60\text{ MHz}$; note 1	85	–	–	dB μ V
		input level for $k = 1\%$ at 40 dB AGC; $f_w = 50\text{ MHz}$; $f_{unw} = 60\text{ MHz}$; note 1	100	–	–	dB μ V

Note

1. Measured in test circuit of Fig.21.

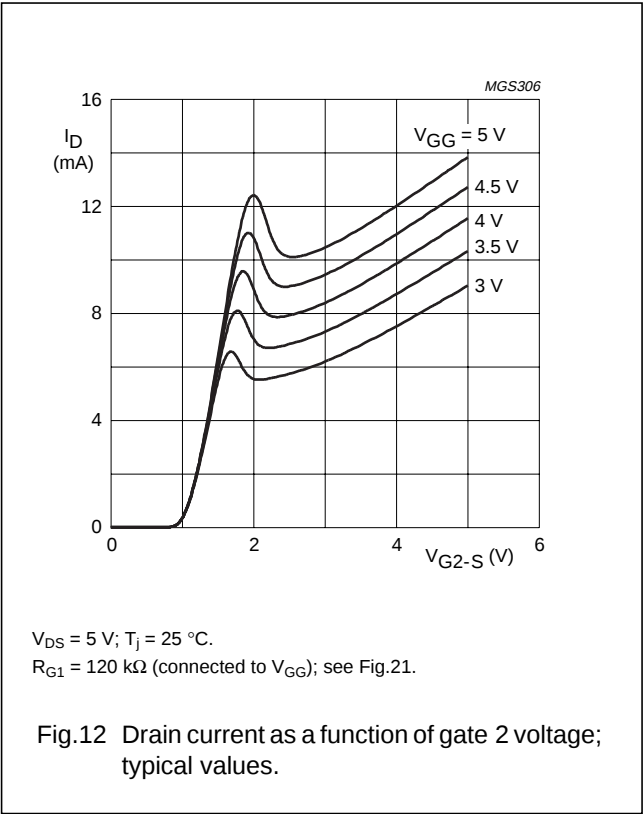
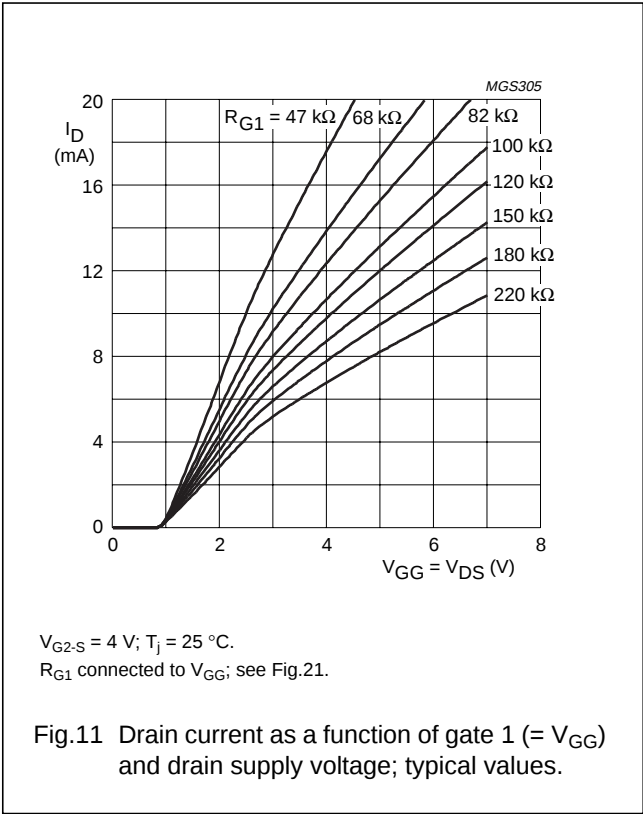
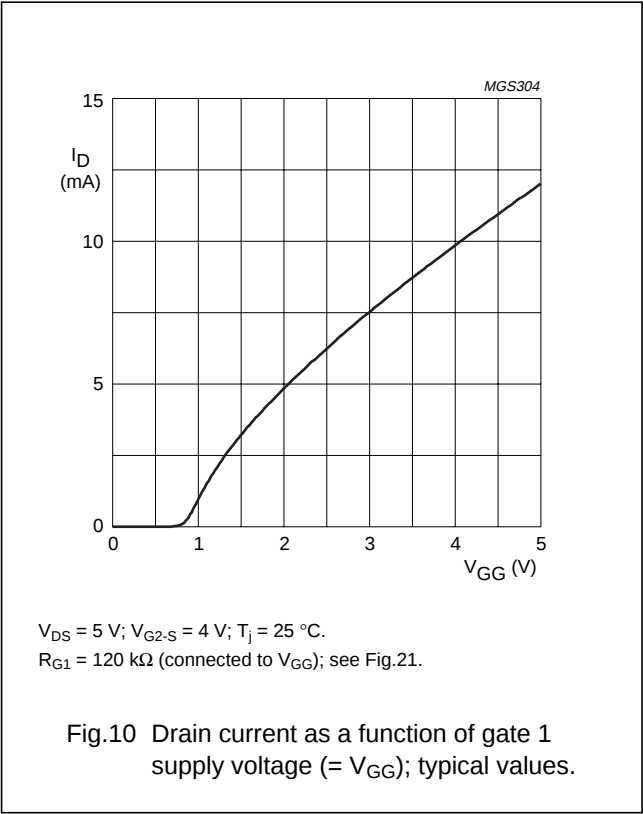
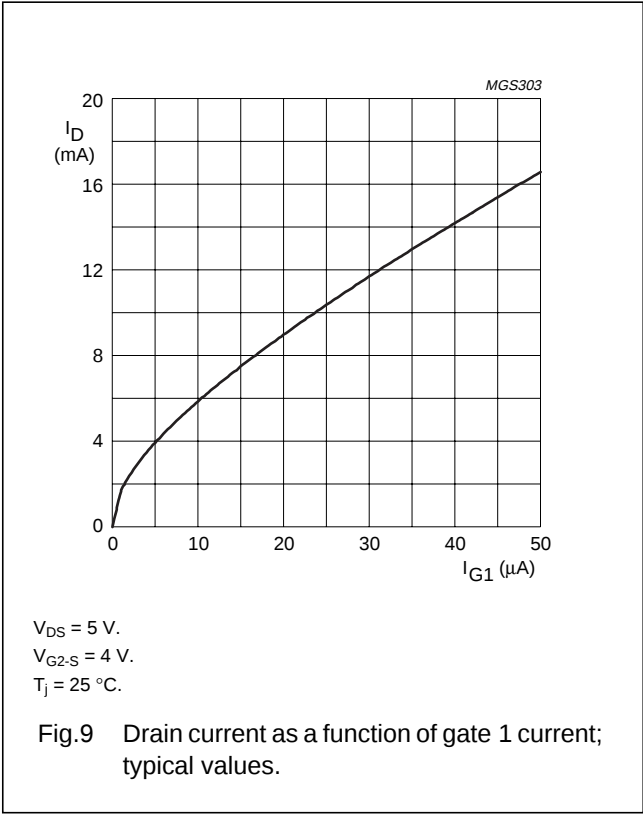
N-channel dual-gate MOS-FETs

BF1101; BF1101R; BF1101WR



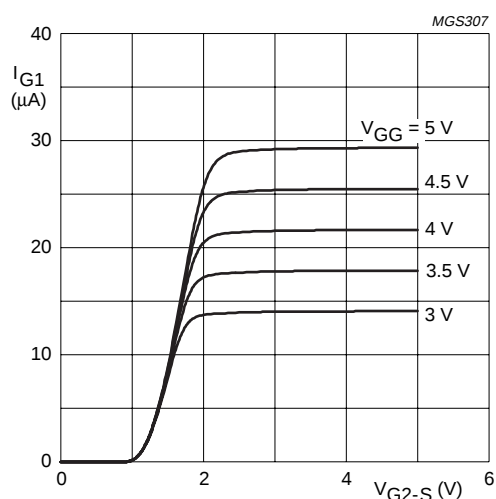
N-channel dual-gate MOS-FETs

BF1101; BF1101R; BF1101WR



N-channel dual-gate MOS-FETs

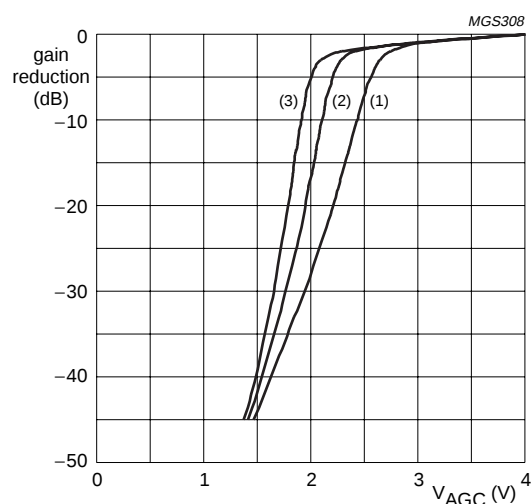
BF1101; BF1101R; BF1101WR



$V_{DS} = 5 \text{ V}$; $T_J = 25^\circ\text{C}$.

$R_{G1} = 120 \text{ k}\Omega$ (connected to V_{GG}); see Fig.21.

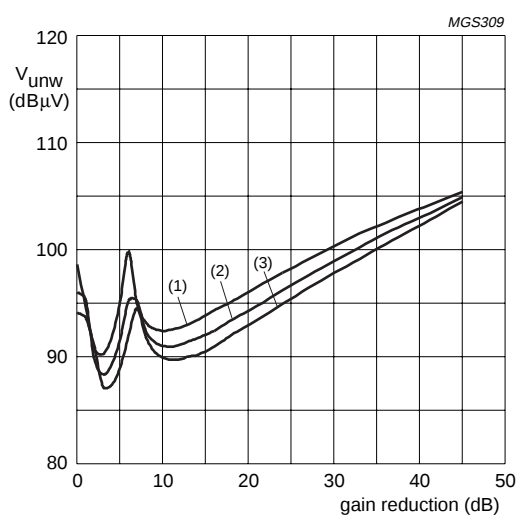
Fig.13 Gate 1 current as a function of gate 2 voltage; typical values.



$V_{DS} = 5 \text{ V}$; $V_{GG} = 5 \text{ V}$; $f = 50 \text{ MHz}$; $T_{amb} = 25^\circ\text{C}$.

(1) $R_{G1} = 68 \text{ k}\Omega$. (2) $R_{G1} = 120 \text{ k}\Omega$. (3) $R_{G1} = 180 \text{ k}\Omega$.

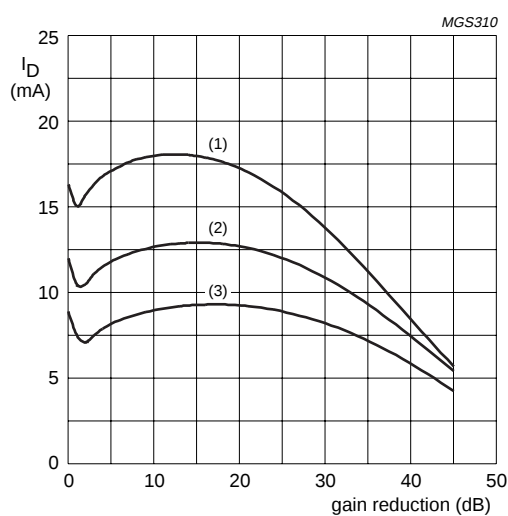
Fig.14 Typical gain reduction as a function of the AGC voltage; see Fig.21.



$V_{DS} = 5 \text{ V}$; $V_{GG} = 5 \text{ V}$; $f = 50 \text{ MHz}$; $f_{unw} = 60 \text{ MHz}$; $T_{amb} = 25^\circ\text{C}$.

(1) $R_{G1} = 68 \text{ k}\Omega$. (2) $R_{G1} = 120 \text{ k}\Omega$. (3) $R_{G1} = 180 \text{ k}\Omega$.

Fig.15 Unwanted voltage for 1% cross-modulation as a function of gain reduction; typical values; see Fig.21.



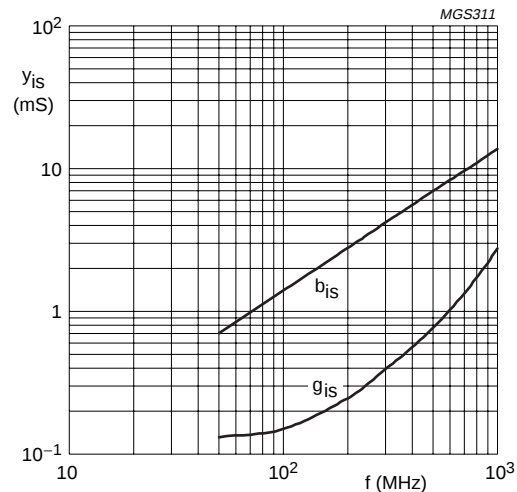
$V_{DS} = 5 \text{ V}$; $V_{GG} = 5 \text{ V}$; $f = 50 \text{ MHz}$; $T_{amb} = 25^\circ\text{C}$.

(1) $R_{G1} = 68 \text{ k}\Omega$. (2) $R_{G1} = 120 \text{ k}\Omega$. (3) $R_{G1} = 180 \text{ k}\Omega$.

Fig.16 Drain current as a function of gain reduction; typical values; see Fig.21.

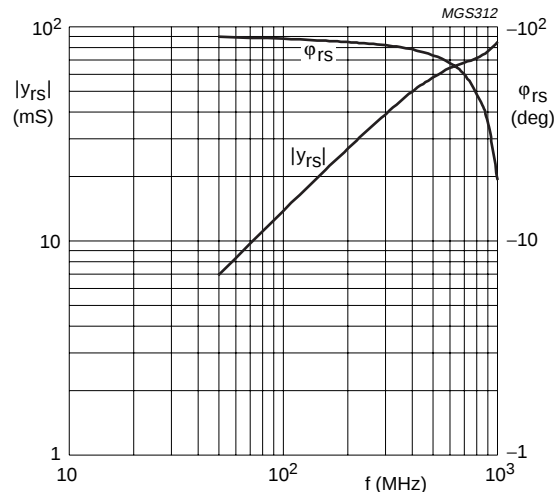
N-channel dual-gate MOS-FETs

BF1101; BF1101R; BF1101WR



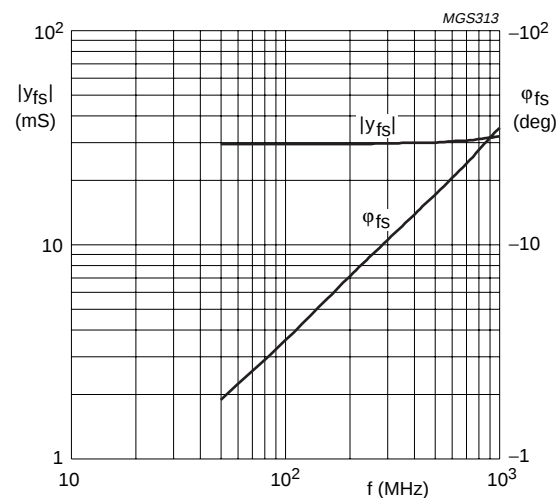
$V_{DS} = 5\text{ V}$; $V_{G2} = 4\text{ V}$.
 $I_D = 12\text{ mA}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Fig.17 Input admittance as a function of frequency; typical values.



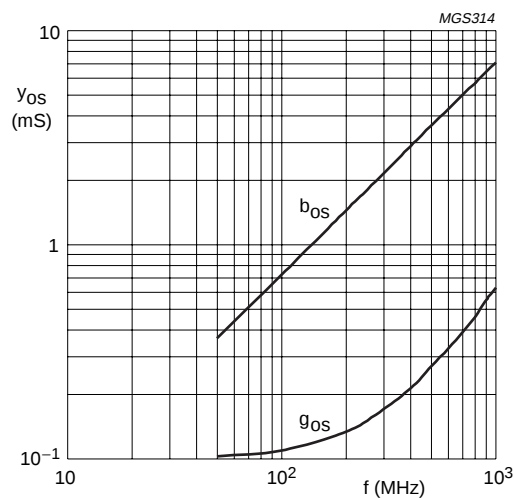
$V_{DS} = 5\text{ V}$; $V_{G2} = 4\text{ V}$.
 $I_D = 12\text{ mA}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Fig.18 Reverse transfer admittance and phase as a function of frequency; typical values.



$V_{DS} = 5\text{ V}$; $V_{G2} = 4\text{ V}$.
 $I_D = 12\text{ mA}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Fig.19 Forward transfer admittance and phase as a function of frequency; typical values.



$V_{DS} = 5\text{ V}$; $V_{G2} = 4\text{ V}$.
 $I_D = 12\text{ mA}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Fig.20 Output admittance as a function of frequency; typical values.

N-channel dual-gate MOS-FETs

BF1101; BF1101R; BF1101WR

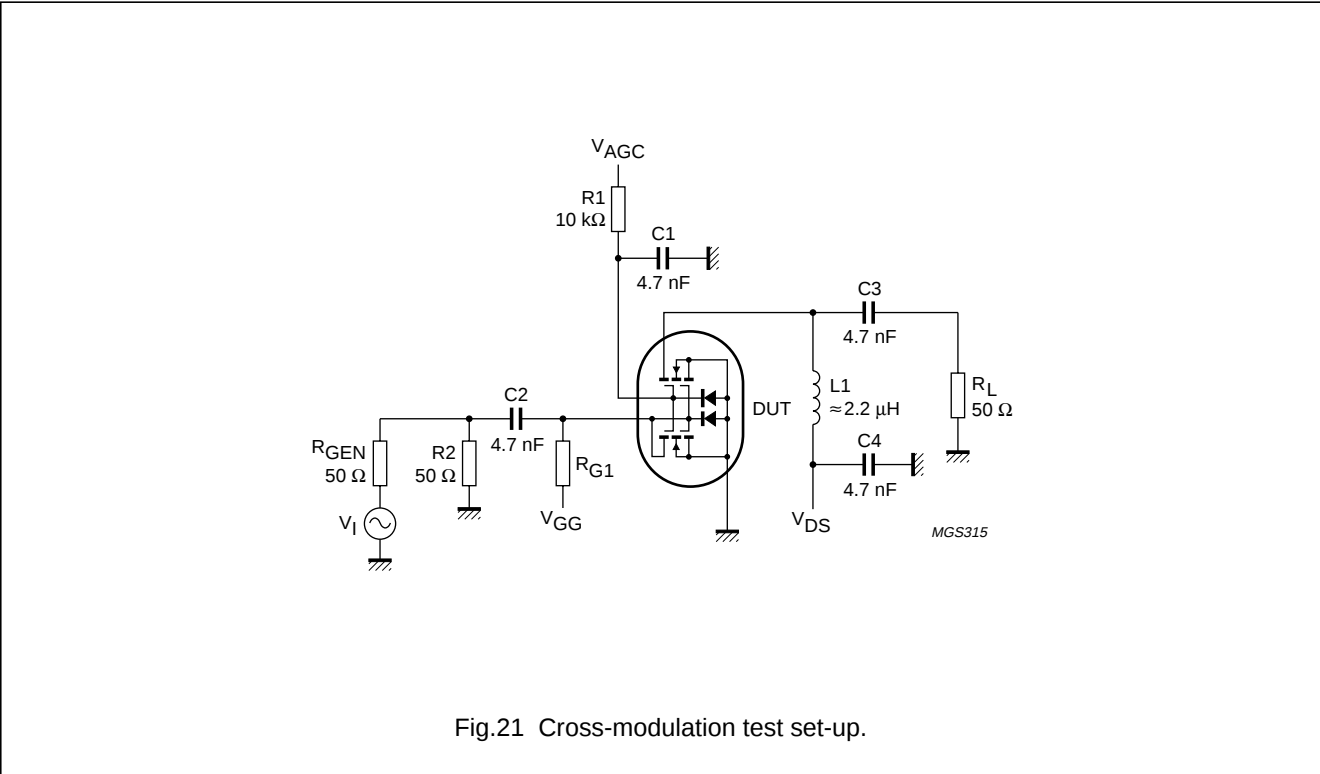


Table 1 Scattering parameters: $V_{DS} = 5\text{ V}$; $V_{G2-S} = 4\text{ V}$; $I_D = 12\text{ mA}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$

f (MHz)	S ₁₁		S ₂₁		S ₁₂		S ₂₂	
	MAGNITUDE (ratio)	ANGLE (deg)	MAGNITUDE (ratio)	ANGLE (deg)	MAGNITUDE (ratio)	ANGLE (deg)	MAGNITUDE (ratio)	ANGLE (deg)
50	0.987	−4.1	2.922	175.0	0.001	87.6	0.990	−2.2
100	0.985	−8.1	2.908	170.3	0.001	86.1	0.989	−4.3
200	0.976	−16.1	2.875	160.8	0.003	83.3	0.985	−8.5
300	0.963	−23.9	2.820	157.6	0.004	80.4	0.982	−12.6
400	0.949	−31.6	2.762	142.6	0.005	78.2	0.977	−16.8
500	0.933	−38.8	2.665	134.1	0.005	77.8	0.972	−20.8
600	0.916	−45.7	2.591	125.7	0.005	78.9	0.967	−24.7
700	0.897	−52.2	2.498	117.7	0.006	81.8	0.961	−28.5
800	0.877	−58.4	2.410	109.6	0.005	89.1	0.957	−32.2
900	0.856	−64.5	2.318	101.6	0.006	97.1	0.950	−35.8
1000	0.832	−70.3	2.214	94.2	0.006	110.4	0.946	−39.6

Table 2 Noise data: $V_{DS} = 5\text{ V}$; $V_{G2-S} = 4\text{ V}$; $I_D = 12\text{ mA}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$

f (MHz)	F _{min} (dB)	Γ _{opt}		R _n (Ω)
		(ratio)	(deg)	
800	1.5	0.715	58.3	37.85

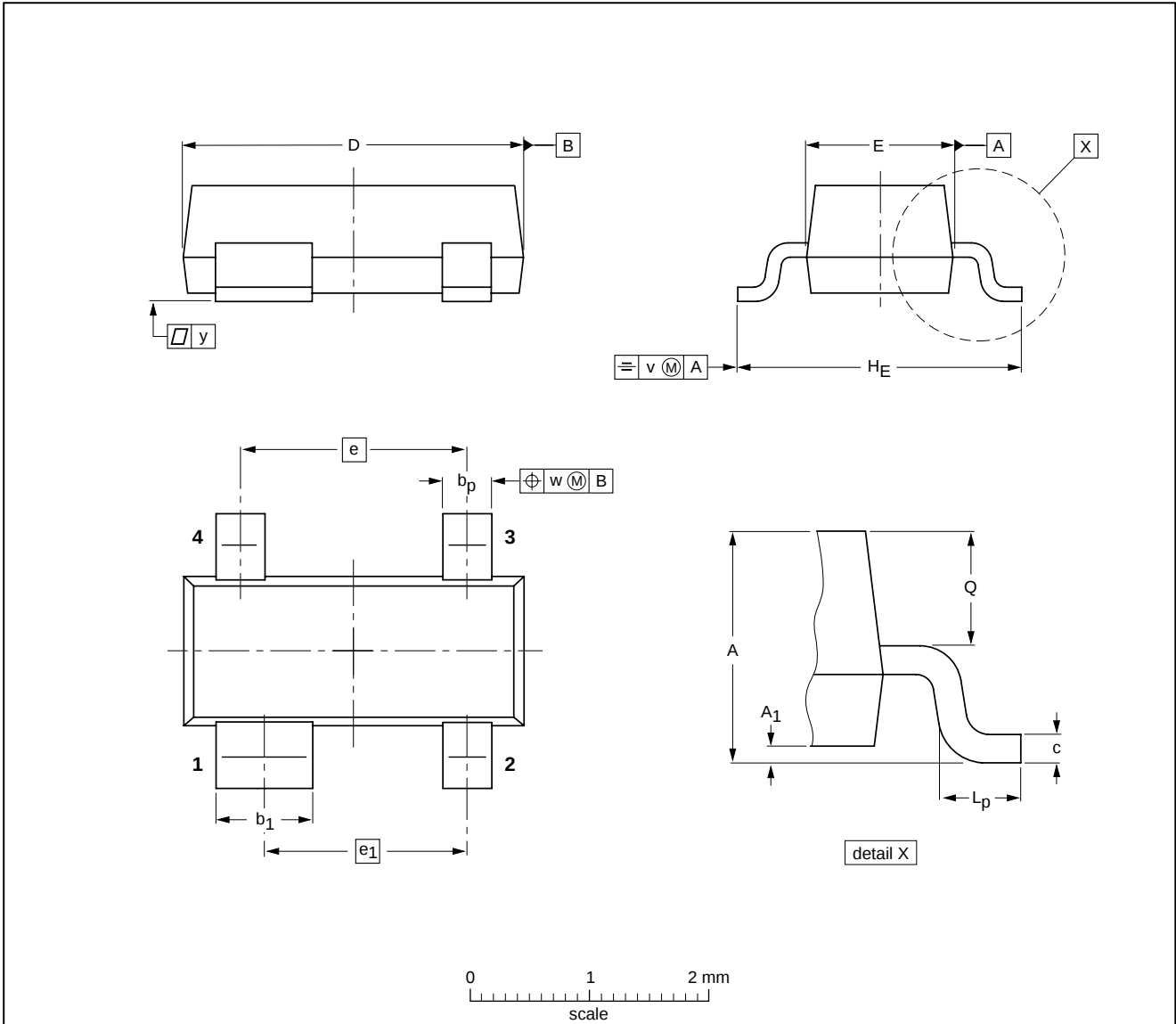
N-channel dual-gate MOS-FETs

BF1101; BF1101R; BF1101WR

PACKAGE OUTLINES

Plastic surface mounted package; 4 leads

SOT143B



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	b ₁	c	D	E	e	e ₁	H _E	L _p	Q	v	w	y
mm	1.1 0.9	0.1	0.48 0.38	0.88 0.78	0.15 0.09	3.0 2.8	1.4 1.2	1.9	1.7	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1	0.1

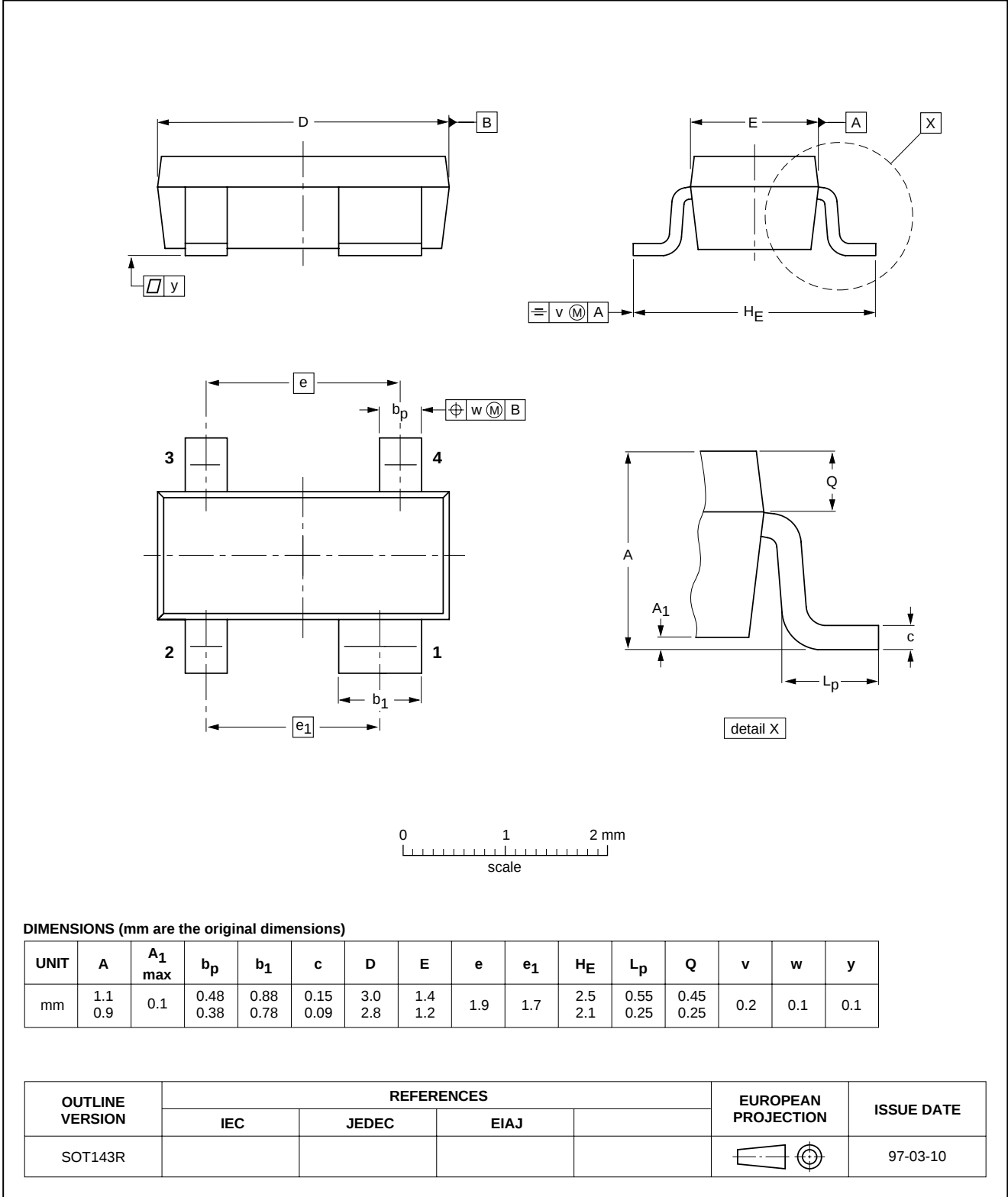
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT143B						97-02-28

N-channel dual-gate MOS-FETs

BF1101; BF1101R; BF1101WR

Plastic surface mounted package; reverse pinning; 4 leads

SOT143R

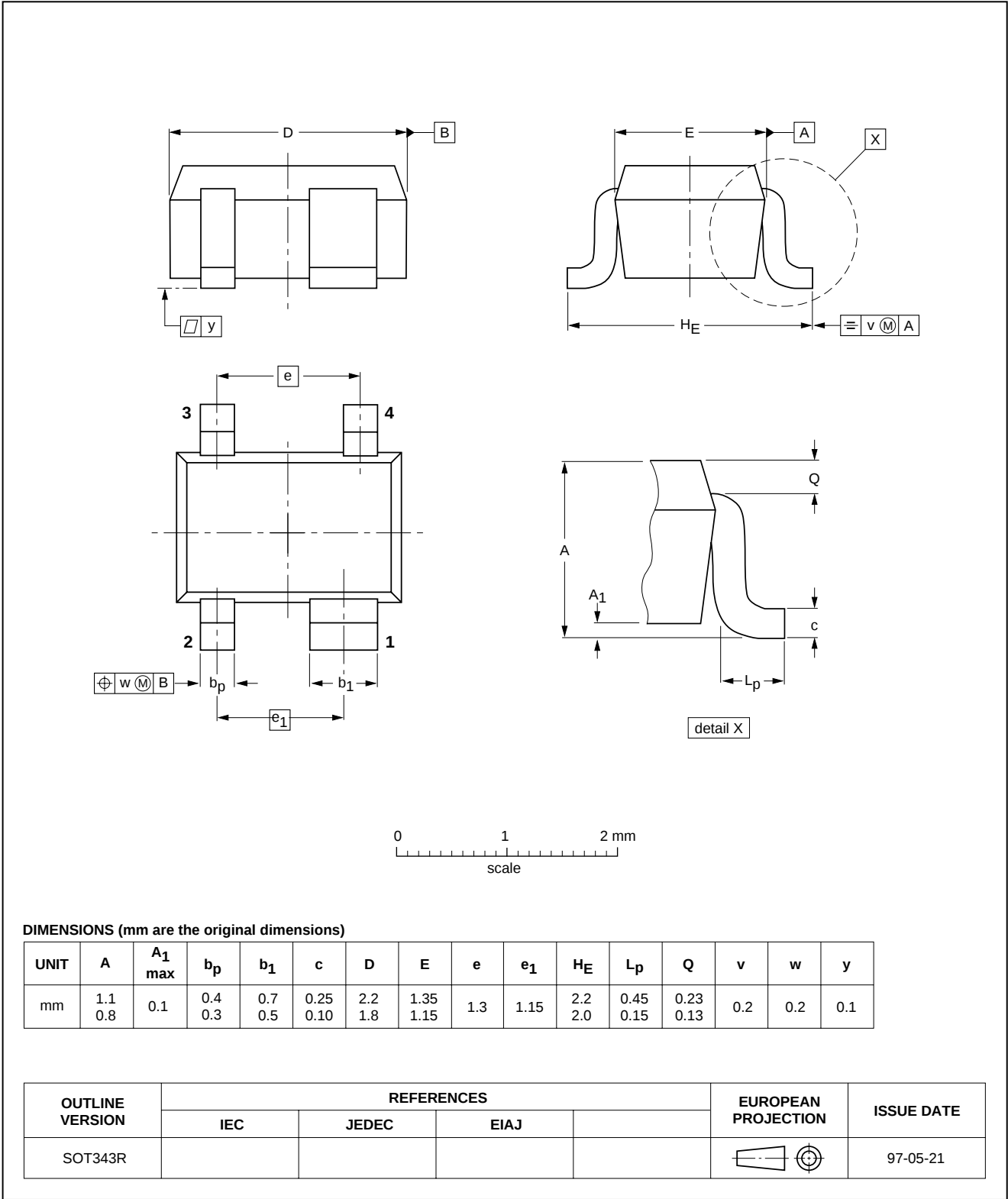


N-channel dual-gate MOS-FETs

BF1101; BF1101R; BF1101WR

Plastic surface mounted package; reverse pinning; 4 leads

SOT343R



N-channel dual-gate MOS-FETs

BF1101; BF1101R; BF1101WR

DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

N-channel dual-gate MOS-FETs

BF1101; BF1101R; BF1101WR

NOTES

N-channel dual-gate MOS-FETs

BF1101; BF1101R; BF1101WR

NOTES

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